

NCV8408, NCV8408B

MAXIMUM RATINGS (T_J = 25 C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V _{DSS}	42	Vdc
Drain-to-Gate Voltage Internally Clamped (R _{GS} = 1.0 MΩ)	V _{DGR}	42	V
Gate-to-Source Voltage	V _{GS}	14	Vdc
Continuous Drain Current	I _D	Internally Limited	
Gate Input Current (V _{GS} = 14 V _{DC})	I _{GS}	10	mA
Source to Drain Current	I _{SD}	4.0	A

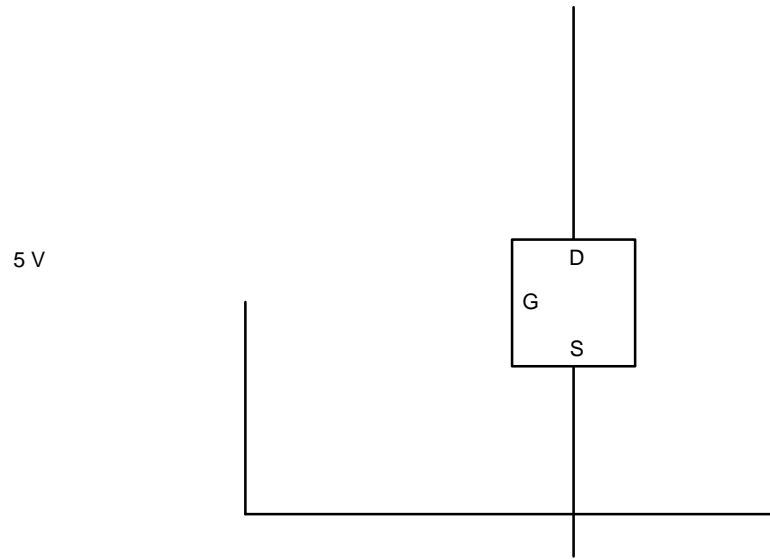
Total Power Dissipation
@ T_A = 25 C (Note 1)
@ T_A

NCV8408, NCV8408B

ELECTRICAL CHARACTERISTICS ($T_J = 25$)

NCV8408, NCV8408B

TEST CIRCUITS AND WAVEFORMS



NCV8408, NCV8408B

TEST CIRCUITS AND WAVEFORMS

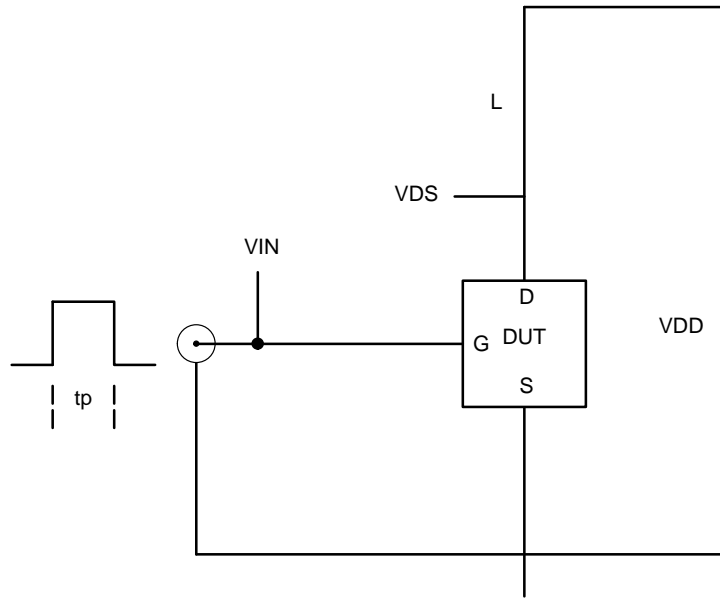


Figure 4. Inductive Load Switching Test Circuit

NCV8408, NCV8408B

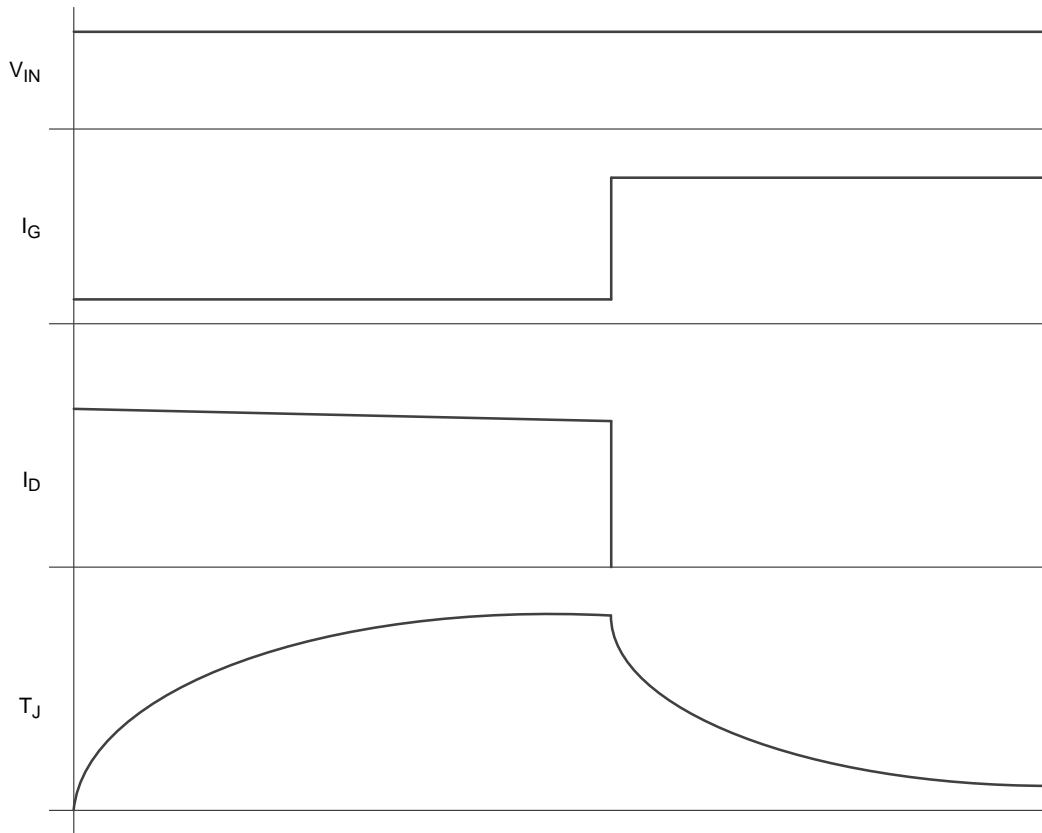


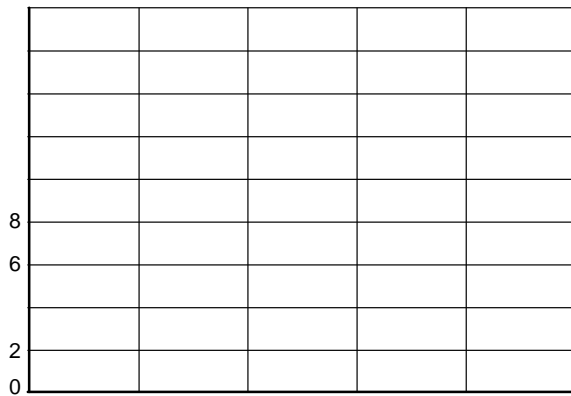
Figure 6. Short-Circuit Protection Behavior



Figure 7. Turn on into Short Circuit Device Response

NCV8408, NCV8408B

TYPICAL CHARACTERISTICS



NCV8408, NCV8408B

TYPICAL CHARACTERISTICS

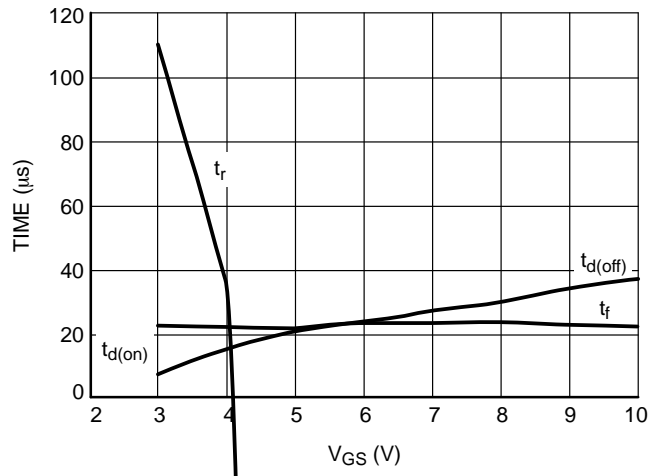
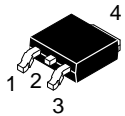


Figure 14. Resistive Switching



SCALE 1:1

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 8: PIN 1. N/C 2. CATHODE 3. ANODE 4. CATHODE	STYLE 9: PIN 1. ANODE 2. CATHODE 3. RESISTOR ADJUST 4. CATHODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

onsemi

onsemi

onsemi

onsemi

— — — — —
— onsemi —
— onsemi —

onsemi

onsemi

onsemi

